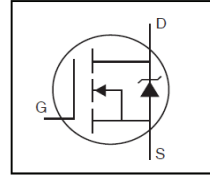
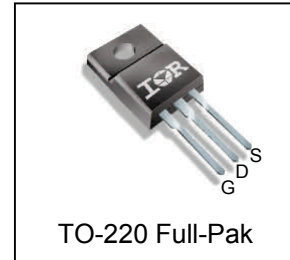


- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

HEXFET® Power MOSFET



| | |
|---------------------------|---------------|
| V_{DSS} | 100V |
| R_{DS(on)} | 0.036Ω |
| I_D | 24A |



| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications

The TO-220 Fullpak eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heatsink using a single clip or by a single screw fixing.

| Base Part Number | Package Type | Standard Pack | | Orderable Part Number |
|------------------|-----------------|---------------|----------|-----------------------|
| | | Form | Quantity | |
| IRFI1310NPbF | TO-220 Full-Pak | Tube | 50 | IRFI1310NPbF |

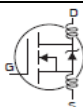
Absolute Maximum Ratings

| Symbol | Parameter | Max. | Units |
|---|--|--------------------|-------|
| I _D @ T _C = 25°C | Continuous Drain Current, V _{GS} @ 10V | 24 | A |
| I _D @ T _C = 100°C | Continuous Drain Current, V _{GS} @ 10V | 17 | |
| I _{DM} | Pulsed Drain Current ①⑥ | 140 | |
| P _D @ T _C = 25°C | Maximum Power Dissipation | 56 | W |
| | Linear Derating Factor | 0.37 | W/°C |
| V _{GS} | Gate-to-Source Voltage | ± 20 | V |
| E _{AS} | Single Pulse Avalanche Energy (Thermally Limited) ②⑥ | 420 | mJ |
| I _{AR} | Avalanche Current ①⑥ | 22 | A |
| E _{AR} | Repetitive Avalanche Energy ① | 5.6 | mJ |
| dv/dt | Peak Diode Recovery dv/dt③⑥ | 5.0 | V/ns |
| T _J | Operating Junction and Storage Temperature Range | -55 to + 175 | °C |
| T _{STG} | | | |
| | | | |
| | Mounting torque, 6-32 or M3 screw | 10 lbf•in (1.1N•m) | |

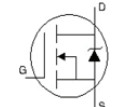
Thermal Resistance

| Symbol | Parameter | Typ. | Max. | Units |
|------------------|---------------------|------|------|-------|
| R _{θJC} | Junction-to-Case | — | 2.7 | °C/W |
| R _{θJA} | Junction-to-Ambient | — | 65 | |

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

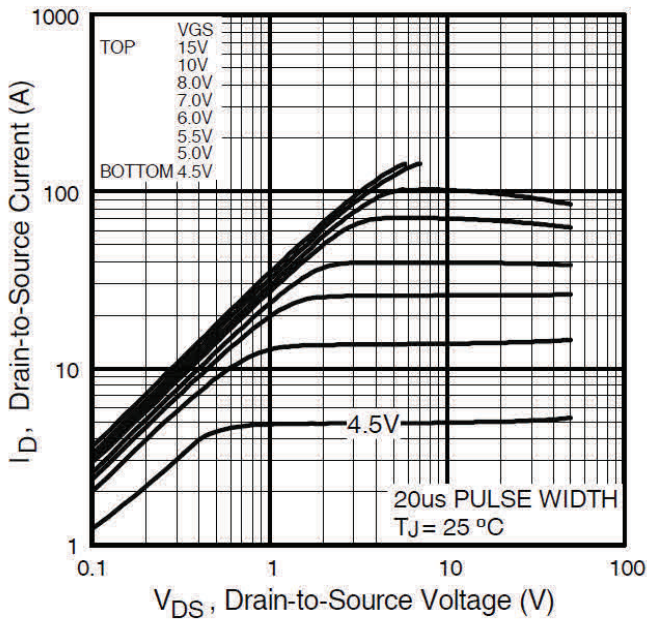
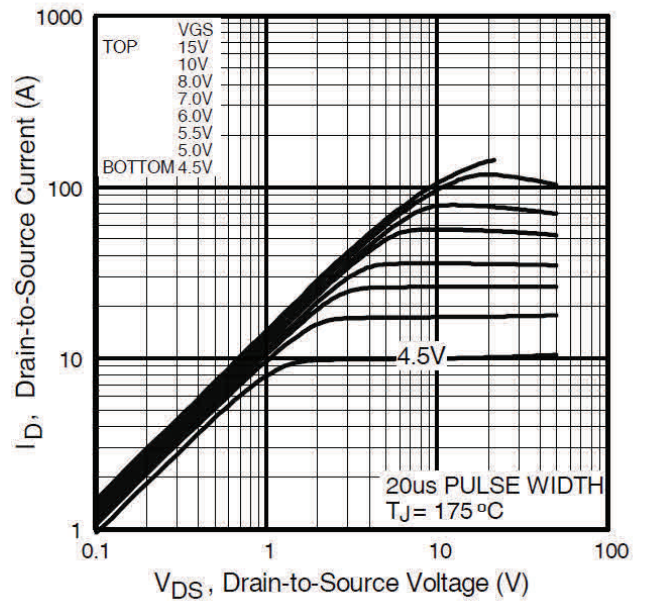
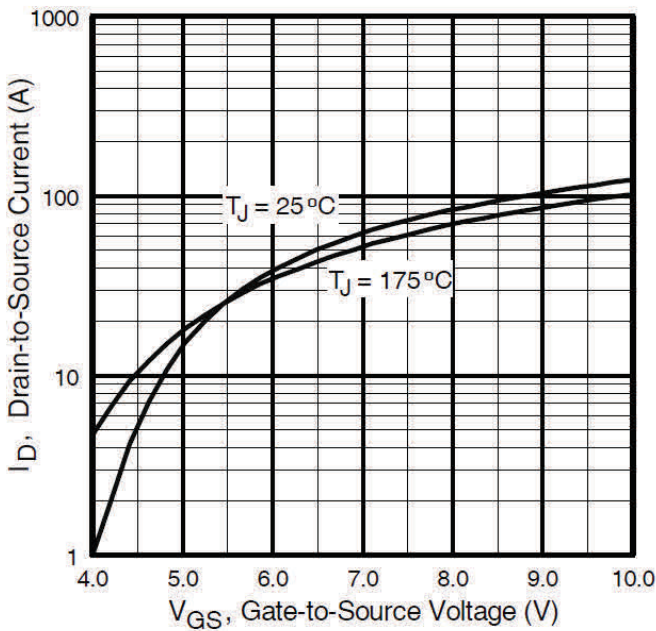
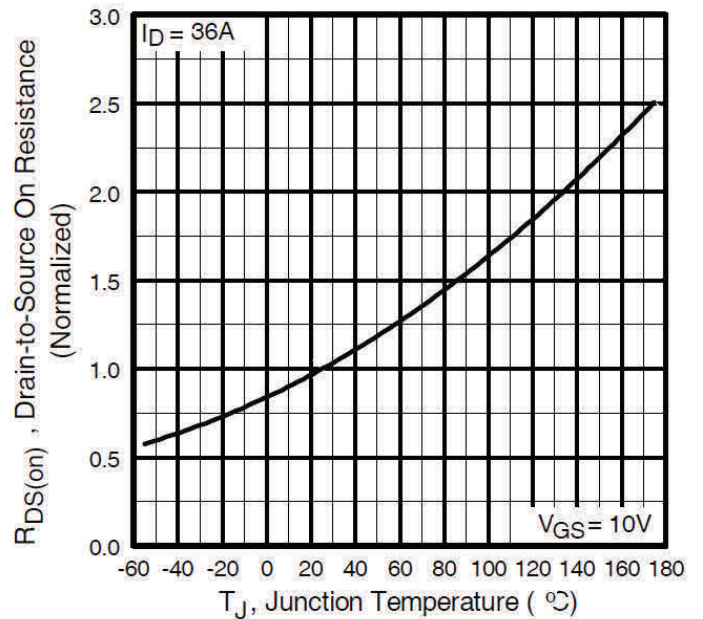
| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--|--------------------------------------|------|------|-------|-------|---|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 100 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS} /ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.11 | — | V/°C | Reference to 25°C, I _D = 1mA ⑥ |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | — | 0.036 | Ω | V _{GS} = 10V, I _D = 13A |
| V _{GS(th)} | Gate Threshold Voltage | 2.0 | — | 4.0 | V | V _{DS} = V _{GS} , I _D = 250μA |
| g _{fs} | Forward Trans conductance | 14 | — | — | S | V _{DS} = 25V, I _D = 22A⑥ |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 25 | μA | V _{DS} = 100 V, V _{GS} = 0V |
| | | — | — | 250 | | V _{DS} = 80V, V _{GS} = 0V, T _J = 150°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -20V |
| Q _g | Total Gate Charge | — | — | 120 | nC | I _D = 22A |
| Q _{gs} | Gate-to-Source Charge | — | — | 15 | | V _{DS} = 80V |
| Q _{gd} | Gate-to-Drain Charge | — | — | 58 | | V _{GS} = 10V, See Fig. 6 and 13④⑥ |
| t _{d(on)} | Turn-On Delay Time | — | 11 | — | ns | V _{DD} = 50V |
| t _r | Rise Time | — | 56 | — | | I _D = 22A |
| t _{d(off)} | Turn-Off Delay Time | — | 45 | — | | R _G = 3.6Ω |
| t _f | Fall Time | — | 40 | — | | R _D = 2.9Ω, See Fig. 10④⑥ |
| L _D | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L _S | Internal Source Inductance | — | 7.5 | — | |  |
| C _{iss} | Input Capacitance | — | 1900 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 450 | — | | V _{DS} = 25V |
| C _{rss} | Reverse Transfer Capacitance | — | 230 | — | | f = 1.0MHz, See Fig. 5⑥ |
| C | Drain to Sink Capacitance | — | 12 | — | | f = 1.0MHz |

Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---|--|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | 24 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | 140 | | |
| V _{SD} | Diode Forward Voltage | — | — | 1.3 | V | T _J = 25°C, I _S = 13A, V _{GS} = 0V ④ |
| t _{rr} | Reverse Recovery Time | — | 180 | 270 | ns | T _J = 25°C, I _F = 22A |
| Q _{rr} | Reverse Recovery Charge | — | 1.2 | 1.8 | μC | di/dt = 100A/μs ④⑥ |
| t _{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D) | | | | |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② starting T_J = 25°C, L = 1.0mH, R_G = 25Ω, I_{AS} = 22A (See fig. 12)
- ③ I_{SD} ≤ 22A, di/dt ≤ 180A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ t = 60s, f = 60Hz
- ⑥ Uses IRF1310N data and test conditions.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Normalized On-Resistance vs. Temperature

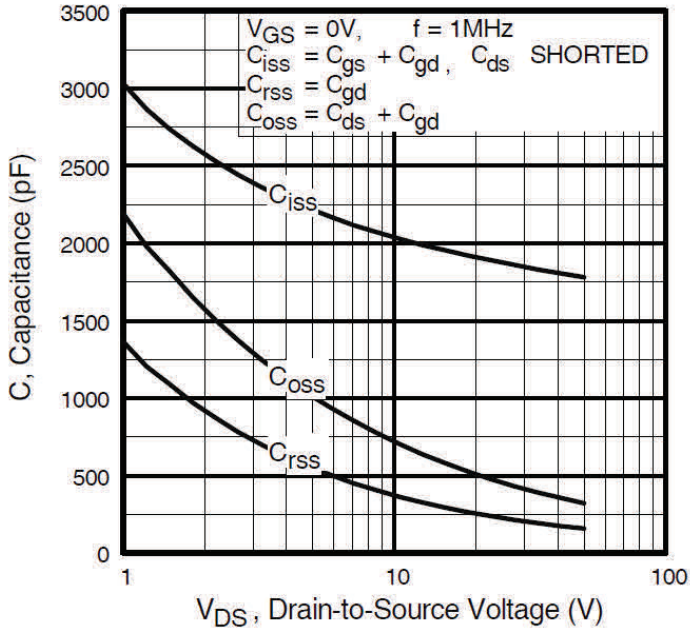


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

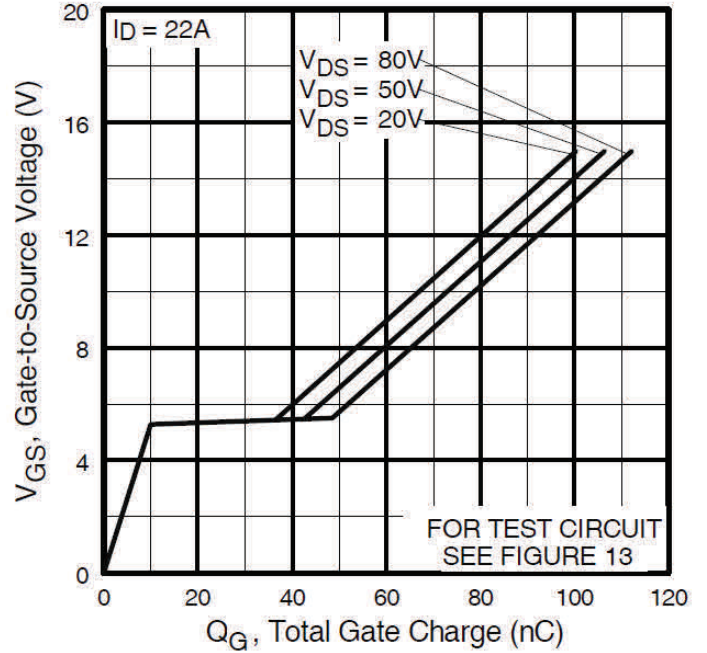


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

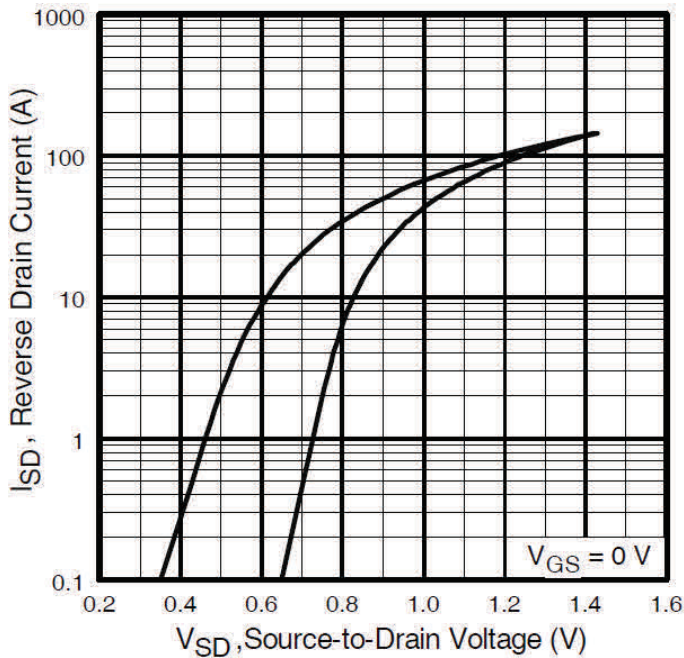


Fig 7 Typical Source-to-Drain Diode Forward Voltage

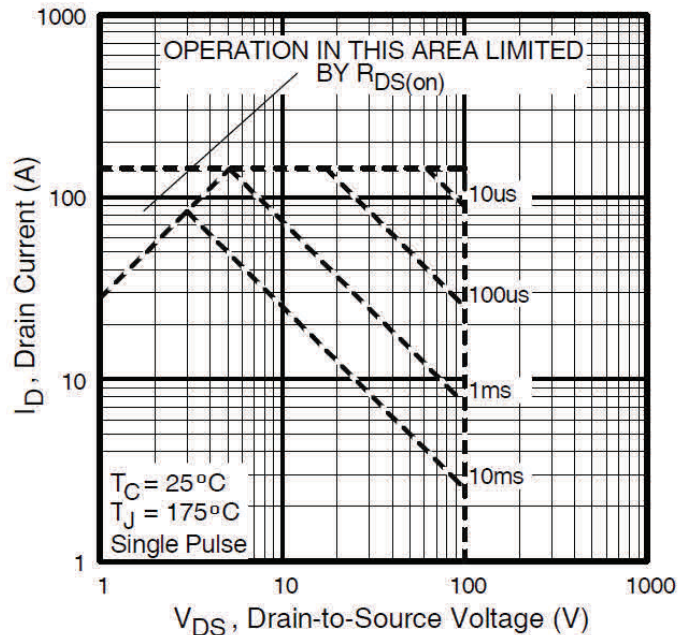


Fig 8. Maximum Safe Operating Area

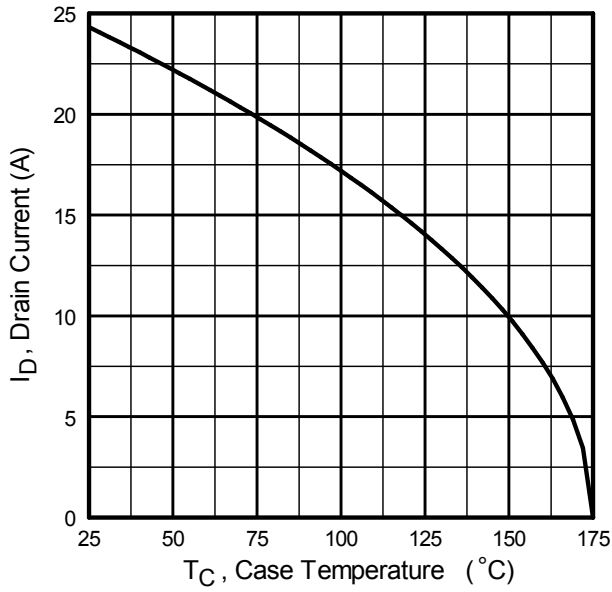
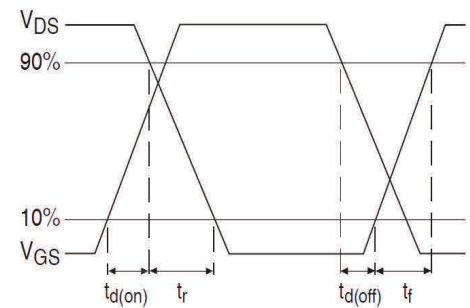
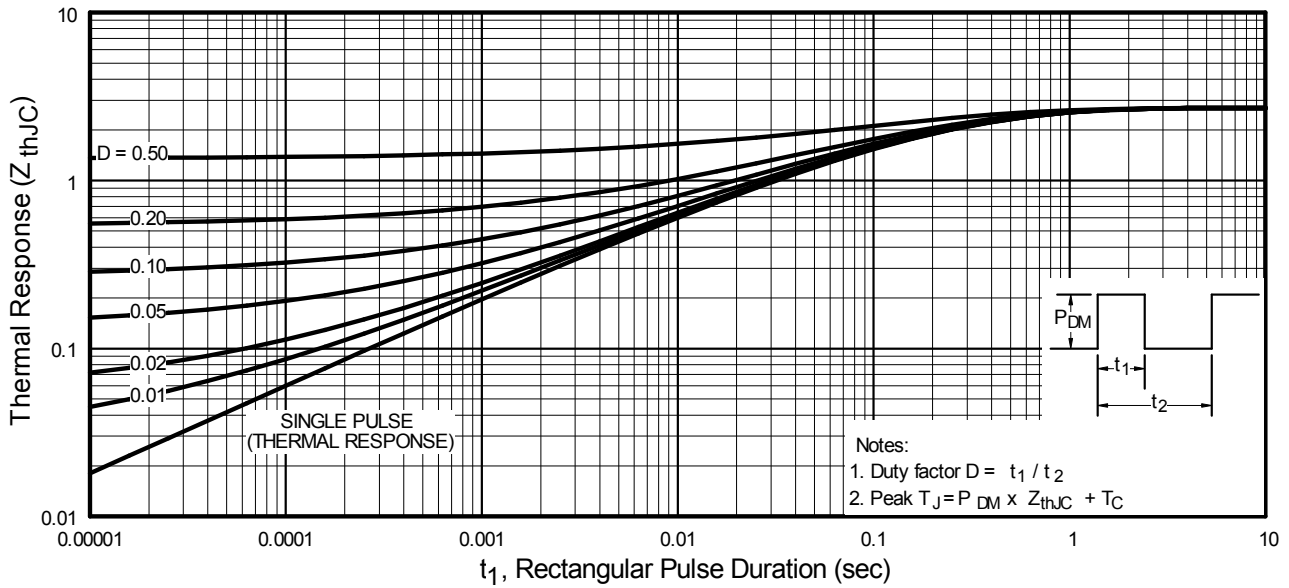
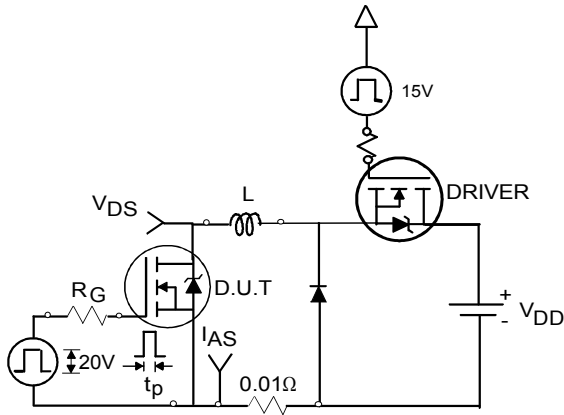
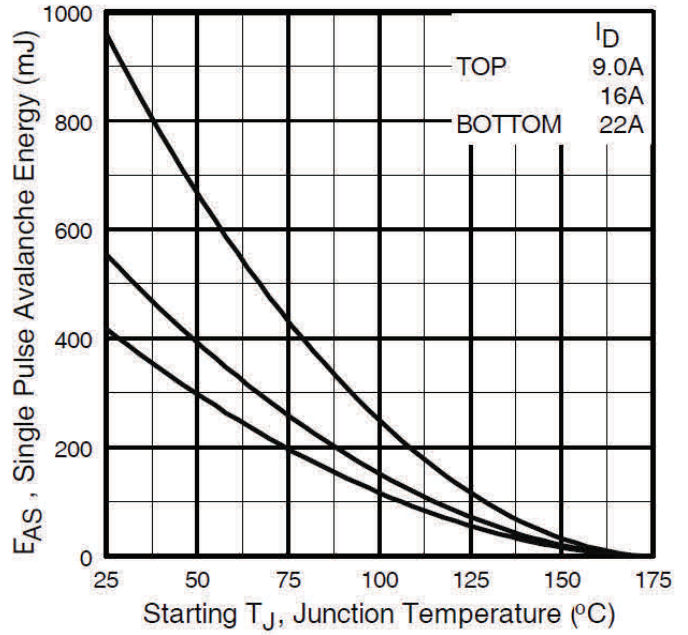
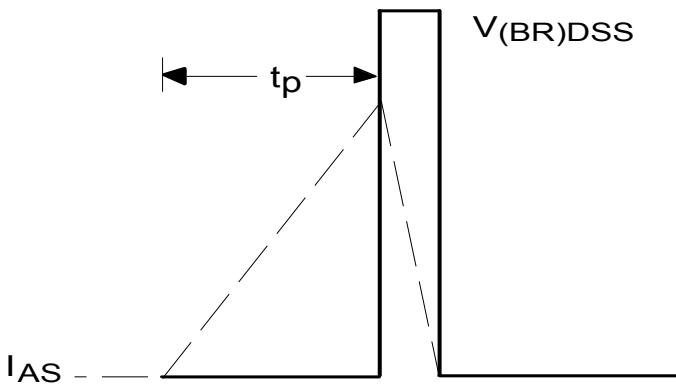
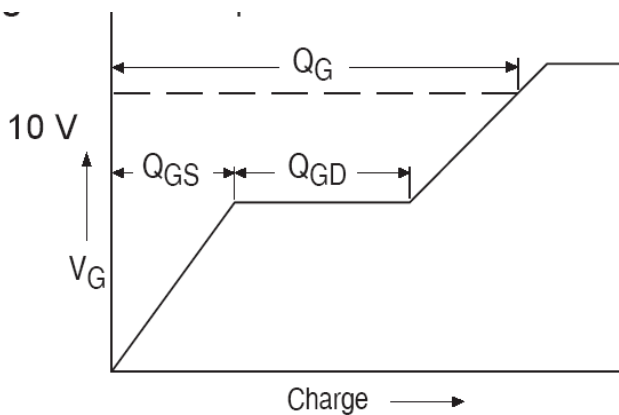
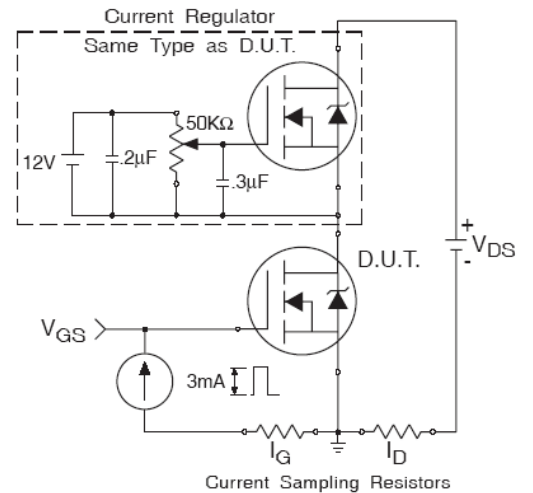

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10a. Switching Time Test Circuit

Fig 10b. Switching Time Waveforms

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig 12a. Unclamped Inductive Test Circuit

Fig 12c. Maximum Avalanche Energy vs. Drain Current

Fig 12b. Unclamped Inductive Waveforms

Fig 13a. Gate Charge Waveform

Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

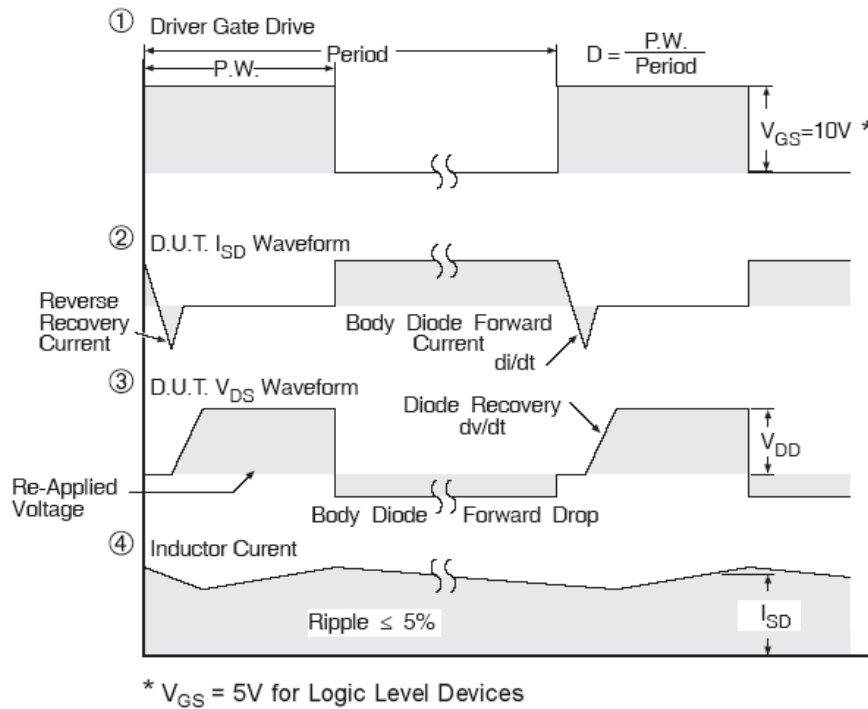
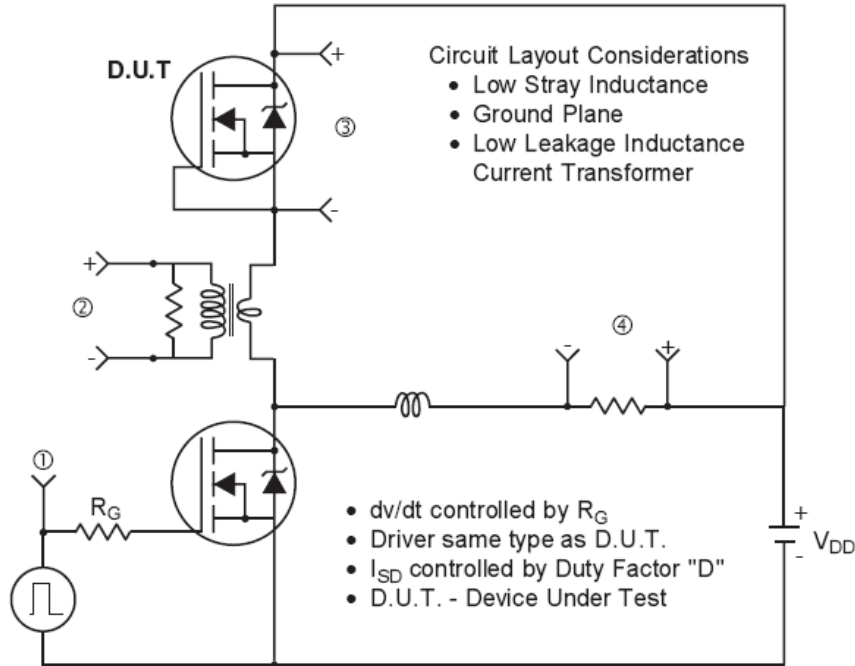
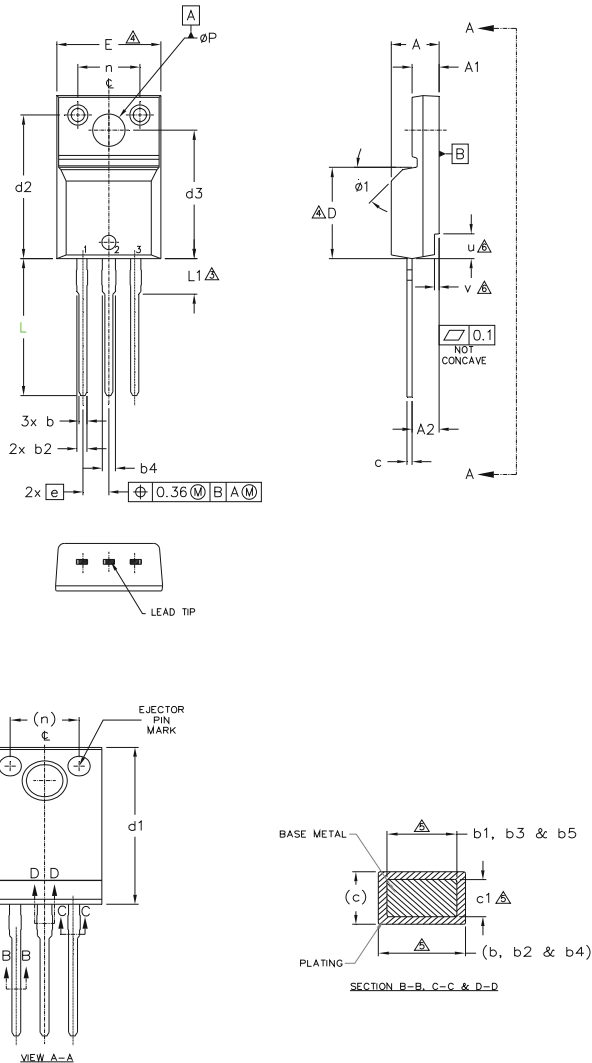


Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

TO-220 Full-Pak Package Outline (Dimensions are shown in millimeters (inches))

NOTES:

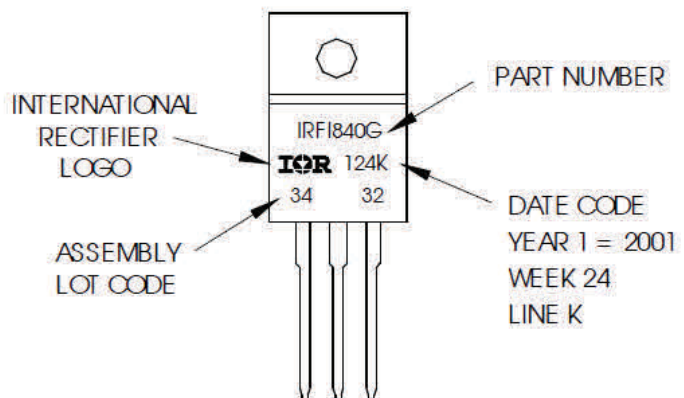
- 1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
- 5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
- 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
- 7.0 CONTROLLING DIMENSION : INCHES.

| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|-------|----------|------|---|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 4.57 | 4.83 | .180 | .190 | LEAD ASSIGNMENTS HEXFET 1.- GATE 2.- DRAIN 3.- SOURCE |
| A1 | 2.57 | 2.82 | .101 | .111 | |
| A2 | 2.51 | 2.92 | .099 | .115 | |
| b | 0.61 | 0.94 | .024 | .037 | |
| b1 | 0.61 | 0.89 | .024 | .035 | |
| b2 | 0.76 | 1.27 | .030 | .050 | |
| b3 | 0.76 | 1.22 | .030 | .048 | |
| b4 | 1.02 | 1.52 | .040 | .060 | |
| b5 | 1.02 | 1.47 | .040 | .058 | |
| c | 0.33 | 0.63 | .013 | .025 | |
| c1 | 0.33 | 0.58 | .013 | .023 | |
| D | 8.66 | 9.80 | .341 | .386 | |
| d1 | 15.80 | 16.13 | .622 | .635 | |
| d2 | 13.97 | 14.22 | .550 | .560 | |
| d3 | 12.29 | 12.93 | .484 | .509 | |
| E | 9.63 | 10.74 | .379 | .423 | 4 |
| e | 2.54 BSC | | .100 BSC | | 3 |
| L | 13.21 | 13.72 | .520 | .540 | 3 |
| L1 | 3.10 | 3.68 | .122 | .145 | |
| n | 6.05 | 6.60 | .238 | .260 | 6 |
| phi P | 3.05 | 3.45 | .120 | .136 | |
| u | 2.39 | 2.49 | .094 | .098 | 6 |
| v | 0.41 | 0.51 | .016 | .020 | 6 |
| phi 1 | - | 45° | - | 45° | |

TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW24, 2001
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to website at <http://www.irf.com/package/>

Qualification Information

| | | |
|-----------------------------------|-------------------------------------|-----|
| Qualification Level | Industrial (per JEDEC JESD47F) † | |
| Moisture Sensitivity Level | TO-220 Full-Pak | N/A |
| RoHS Compliant | Yes | |

† Applicable version of JEDEC standard at the time of product release.

Revision History

| Date | Comments |
|------------|--|
| 5/27/2016 | <ul style="list-style-type: none"> Updated datasheet with corporate template. Added disclaimer on last page. |
| 04/27/2017 | <ul style="list-style-type: none"> Corrected Package Outline on page 8. |

Trademarks of Infineon Technologies AG

μHVIC™, μIPM™, μPFC™, AU-ConvertIR™, AURIX™, C166™, CanPAK™, CIPOS™, CIPURSE™, CoolDP™, CoolGaN™, COOLiR™, CoolMOST™, CoolSET™, CoolSiC™, DAVE™, DI-POL™, DirectFET™, DrBlade™, EasyPIM™, EconoBRIDGE™, EconoDUAL™, EconoPACK™, EconoPIM™, EiceDRIVER™, eupec™, FCOS™, GaNpowIR™, HEXFET™, HITFET™, HybridPACK™, iMOTION™, IRAM™, ISOFACE™, IsoPACK™, LEDrivIR™, LITIX™, MIPAQ™, ModSTACK™, my-d™, NovalithIC™, OPTIGA™, OptiMOST™, ORIGA™, PowIRaudio™, PowIRStage™, PrimePACK™, PrimeSTACK™, PROFET™, PRO-SiL™, RASIC™, REAL3™, SmartLEWIS™, SOLID FLASH™, SPOC™, StrongIRFET™, SupIRBuck™, TEMPFET™, TRENCHSTOP™, TriCore™, UHVIC™, XHP™, XMC™

Trademarks updated November 2015

Other Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2016-04-19

Published by
Infineon Technologies AG
81726 Munich, Germany

© 2016 Infineon Technologies AG.
All Rights Reserved.

Do you have a question about this document?
Email: erratum@infineon.com

Document reference
ifx1

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or **characteristics ("Beschaffheitsgarantie")**.

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document **is subject to customer's compliance with its obligations** stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in **customer's applications**.

The data contained in this document is exclusively intended for technically trained staff. It is the **responsibility of customer's technical departments** to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).

Please note that this product is not qualified according to the AEC Q100 or AEC Q101 documents of the Automotive Electronics Council.

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, **Infineon Technologies' products may not be used** in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Infineon:](#)

[IRFI1310NPBF](#)